

# **STB75NF75 STP75NF75 - STP75NF75FP**

N-channel 75V - 0.0095Ω - 80A - TO-220 - TO-220FP - D<sup>2</sup>PAK STripFET™ II Power MOSFET

#### **General features**

Туре	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB75NF75	75V	<0.011Ω	80A <sup>(1)</sup>
STP75NF75	75V	<0.011Ω	80A <sup>(1)</sup>
STP75NF75FP	75V	<0.011Ω	80A <sup>(1)</sup>

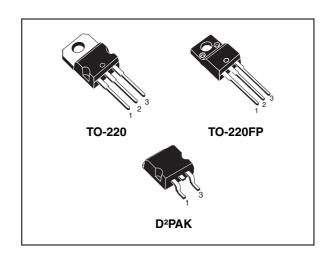
- 1. Current limited by package
- Exceptional dv/dt capability
- 100% avalanche tested

### **Description**

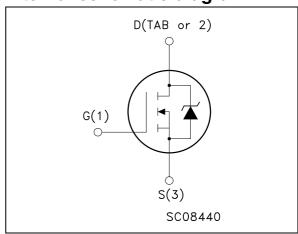
This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

## **Applications**

■ Switching application



## Internal schematic diagram



#### **Order codes**

Part number	Part number Marking		Packaging
STB75NF75T4	B75NF75	D²PAK	Tape & reel
STP75NF75	P75NF75	TO-220	Tube
STP75NF75FP	P75NF75	TO-220FP	Tube

February 2007 Rev 8 1/16

# **Contents**

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# 1 Electrical ratings

Table 1. Absolute maximum ratings

Cymbal	Drain-gate voltage ( $R_{GS} = 20K\Omega$ ) $R_{GS}$ Gate-source voltage  Drain current (continuous) at $T_C = 25^{\circ}C$ Drain current (continuous) at $T_{C} = 100^{\circ}C$ Drain current (pulsed)  Total dissipation at $T_C = 25^{\circ}C$ Derating factor $R_{CS}$ Peak diode recovery voltage slope $R_{CS}$ Single pulse avalanche energy  Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; $T_C = 25^{\circ}C$	Valu	Unit	
Symbol	Parameter	D <sup>2</sup> PAK /TO-220	TO-220FP	Unit
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	75		V
V <sub>DGR</sub>	Drain-gate voltage ( $R_{GS} = 20K\Omega$ )	75		٧
V <sub>GS</sub>	Gate-source voltage	± 20	)	٧
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> = 25°C	80	80	Α
I <sub>D</sub> <sup>(1)</sup>	Drain current (continuous) at T <sub>C</sub> =100°C	70	70	Α
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	320	320	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25°C	300	45	W
	Derating factor	2.0	0.3	W/°C
dv/dt (3)	Peak diode recovery voltage slope	12		V/ns
E <sub>AS</sub> (4)	Single pulse avalanche energy	700		mJ
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s; $T_C$ =25°C)	2000		٧
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to	175	°C

- 1. Current limited by package
- 2. Pulse width limited by safe operating area
- 3.  $I_{SD} \leq 80A$ ,  $di/dt \leq 300A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{JMAX}$
- 4. Starting  $T_J = 25$  °C,  $I_D = 40A$ ,  $V_{DD} = 37.5V$

Table 2. Thermal data

Cumbal	Parameter	Value	Unit	
Symbol	Parameter	D <sup>2</sup> PAK /TO-220	TO-220FP	Unit
R <sub>thJC</sub>	Thermal resistance junction-case max	0.5	3.33	°C/W
R <sub>thJA</sub>	Thermal resistance junction-ambient max	62.5		°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose <sup>(1)</sup>	300		°C

1. 1.6mm from case for 10sec)

# 2 Electrical characteristics

(T<sub>CASE</sub>=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	75			٧
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS} = Max rating,$ $V_{DS} = Max rating @ 125°C$			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	٧
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 40A		0.0095	0.011	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> (1)	Forward transconductance	$V_{DS} = 15V, I_D = 40A$		20		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> =25V, f = 1 MHz, V <sub>GS</sub> = 0		3700 730 240		pF pF pF
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 60V, I_{D} = 80A$ $V_{GS} = 10V$		117 27 47	160	nC nC nC

<sup>1.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}$ = 37.5V, $I_{D}$ = 45A, $R_{G}$ =4.7 $\Omega$ , $V_{GS}$ =10V Figure 15 on page 9		25 100 66 30		ns ns ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current				80	Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)				320	Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	$I_{SD} = 80A, V_{GS} = 0$			1.5	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80A$ , $di/dt = 100A/\mu s$ , $V_{DD} = 25V$ , $T_{J} = 150^{\circ}C$ Figure 17 on page 9		132 660 10		ns nC A

<sup>1.</sup> Pulse width limited by safe operating area

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<sup>2.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 - Figure 2. Thermal impedancefor TO-220 - D²PAK D²PAK

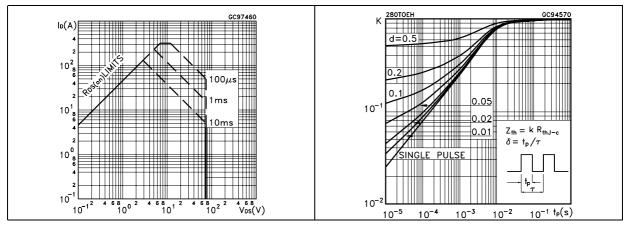


Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

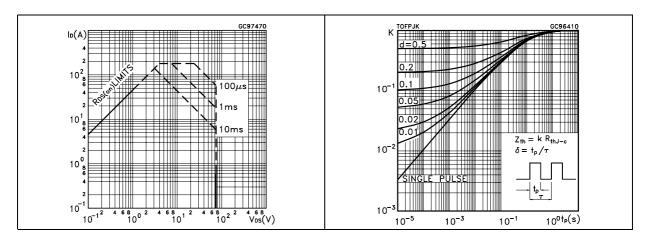
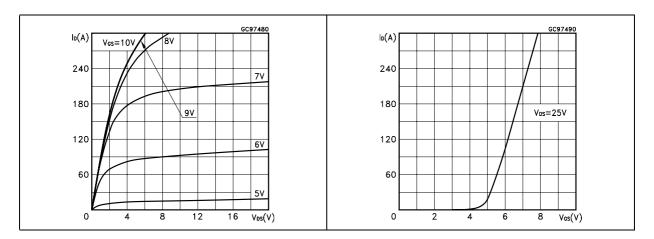


Figure 5. Output characterisics

Figure 6. Transfer characteristics



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Figure 7. Transconductance

Figure 8. Static drain-source on resistance

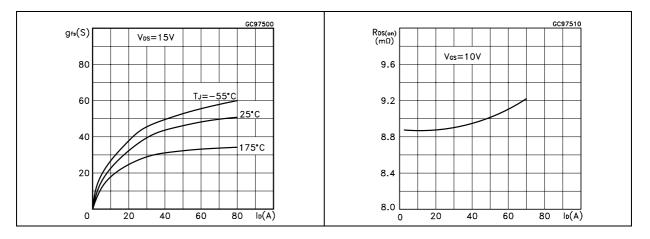


Figure 9. Gate charge vs gate-source voltage Figure 10. Capacitance variations

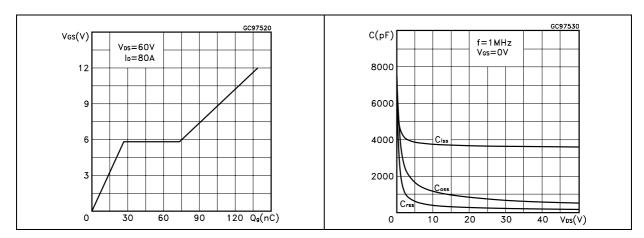


Figure 11. Normalized gate threshold voltage Figure 12. Normalized on resistance vs vs temperature temperature

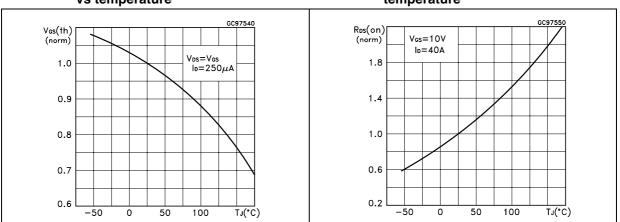
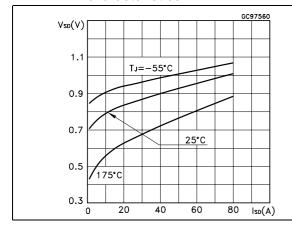
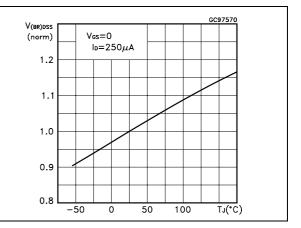


Figure 13. Source-drain diode forward characteristics

Figure 14. Normalized  $\mathbf{B}_{\text{VDSS}}$  vs temperature





## 3 Test circuit

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

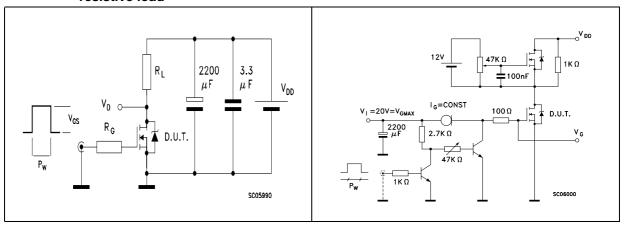


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped inductive load test circuit

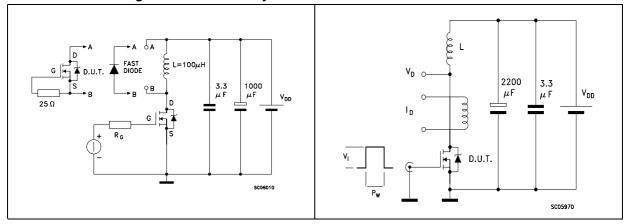
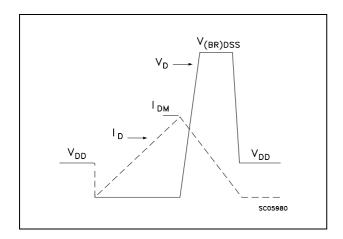


Figure 19. Unclamped inductive waveform

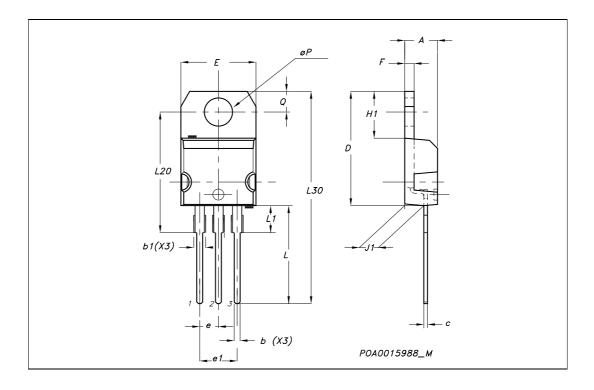


# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>

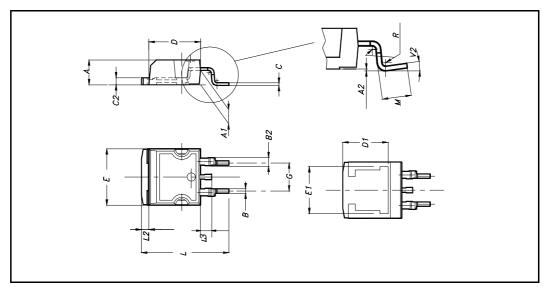
### **TO-220 MECHANICAL DATA**

DIM.		mm.			inch			
DIW.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α	4.40		4.60	0.173		0.181		
b	0.61		0.88	0.024		0.034		
b1	1.15		1.70	0.045		0.066		
С	0.49		0.70	0.019		0.027		
D	15.25		15.75	0.60		0.620		
Е	10		10.40	0.393		0.409		
е	2.40		2.70	0.094		0.106		
e1	4.95		5.15	0.194		0.202		
F	1.23		1.32	0.048		0.052		
H1	6.20		6.60	0.244		0.256		
J1	2.40		2.72	0.094		0.107		
L	13		14	0.511		0.551		
L1	3.50		3.93	0.137		0.154		
L20		16.40			0.645			
L30		28.90			1.137			
øΡ	3.75		3.85	0.147		0.151		
Q	2.65		2.95	0.104		0.116		



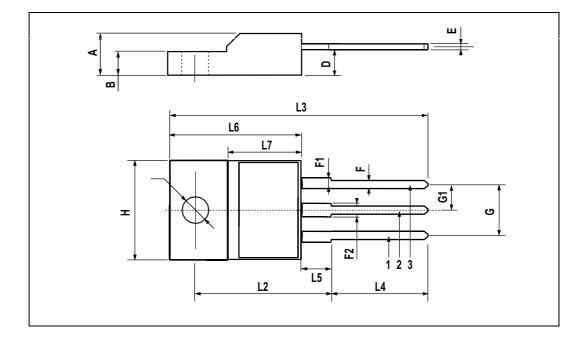
# D<sup>2</sup>PAK MECHANICAL DATA

DIM.		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	O <sub>0</sub>		4º			

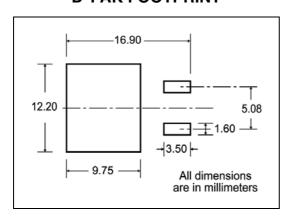


### **TO-220FP MECHANICAL DATA**

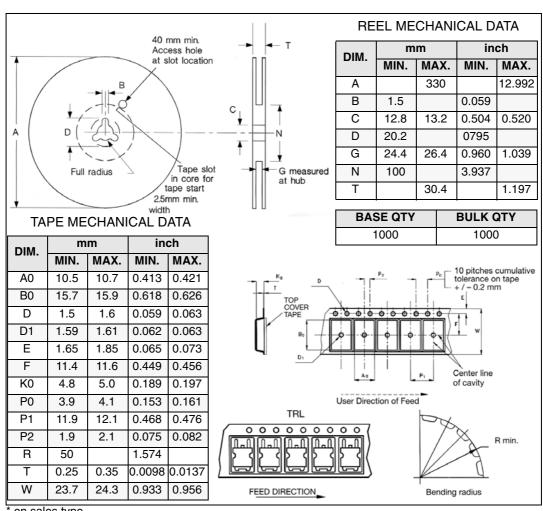
DIM	mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



# 5 Packaging mechanical data D<sup>2</sup>PAK FOOTPRINT



#### TAPE AND REEL SHIPMENT



# 6 Revision history

Table 7. Revision history

Date	Revision	Changes
03-Aug-2006	6	Complete version
15-Sep-2006	7	R <sub>DS(on)</sub> value update
27-Feb-2007	8	The document has been reformatted

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